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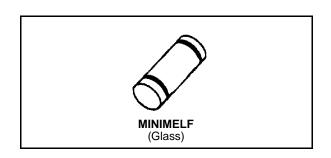


## SMALL SIGNAL SCHOTTKY DIODE

### **DESCRIPTION**

General purpose metal to silicon diode featuring very low turn-on voltage and fast switching.

This device has integrated protection against excessive voltage such as electrostatic discharges.



## **ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit	
$V_{RRM}$	Repetitive Peak Reverse Voltage	100	V	
I <sub>F</sub>	Forward Continuous Current	100	mA	
I <sub>FRM</sub>	$\begin{array}{ll} \text{Repetitive Peak Forward Current} & & t_p \leq 1s \\ & \delta \leq 0.5 \end{array}$		350	mA
I <sub>FSM</sub>	Surge non Repetitive Forward Current t <sub>p</sub> = 10ms		750	mA
P <sub>tot</sub>	Power Dissipation	100	mW	
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range	- 65 to + 150 - 65 to + 125	°C °C	
TL	Maximum Temperature for Soldering during	260	°C	

## THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R <sub>th(j-l)</sub>	Junction-leads	300	°C/W

### **ELECTRICAL CHARACTERISTICS**

## STATIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
$V_{BR}$	T <sub>j</sub> = 25°C	$I_R = 100 \mu A$		100			V
V <sub>F</sub> *	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1mA	I <sub>F</sub> = 1mA		0.4	0.45	V
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 200mA				1	
I <sub>R</sub> *	T <sub>j</sub> = 25°C		V <sub>R</sub> = 50V			0.1	μА
	T <sub>j</sub> = 100°C					20	

## DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Тур.	Max.	Unit
С	$T_j = 25^{\circ}C$ $V_R = 10^{\circ}$	f = 1MHz		2		pF

<sup>\*</sup> Pulse test:  $t_p \le 300 \mu s \delta < 2\%$ .

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Figure 1. Forward current versus forward voltage at different temperatures (typical values).

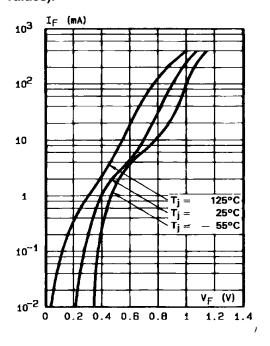


Figure 2. Forward current versus forward voltage (typical values).

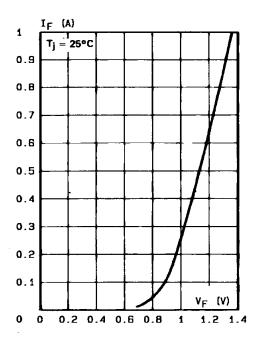


Figure 3. Reverse current versus junction temperature.

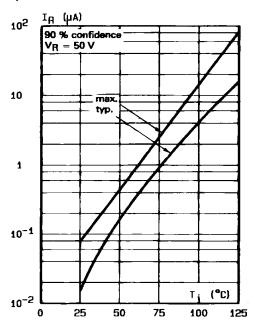
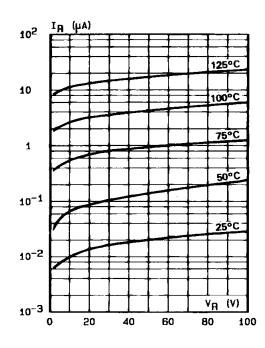
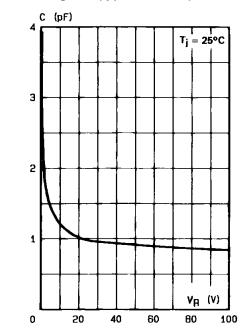


Figure 4. Reverse current versus continuous reverse voltage (typical values).



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Figure 5. Capacitance C versus reverse applied voltage  $V_{\mbox{\scriptsize R}}$  (typical values).

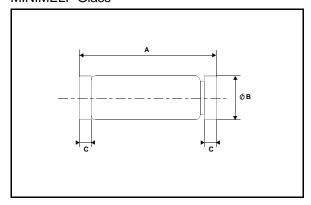


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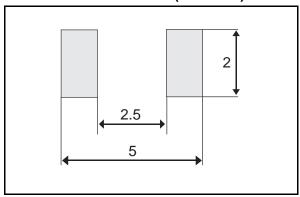
#### PACKAGE MECHANICAL DATA

### **MINIMELF Glass**



	DIMENSIONS					
REF.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	3.30	3.40	3.6	0.130	0.134	0.142
В	1.59	1.60	1.62	0.063	0.063	0.064
С	0.40	0.45	0.50	0.016	0.018	0.020
D		1.50			0.059	

#### **FOOT PRINT DIMENSIONS (Millimeter)**



Marking: ring at cathode end. Weight: 0.05g

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